

Substitute for form 1449A/B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)				<b>Complete if Known</b>	
Application Number		NEW- 101736617			
Filing Date		December 12, 2003			
First Named Inventor		Kristy A. Campbell			
Art Unit		N/A 2829B			
Examiner Name		Not Yet Assigned V. Yevsikov			
Attorney Docket Number		M4065.0698/P698-A			
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Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)				
✓	AA	6,473,332		10/2002	Ignatiev et al.	
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Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>4</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
✓	BA	WO	97/48032	12/18/1997	Kozicki et al.		
✓	BB	WO	99/28914	06/10/1999	Kozicki et al.		

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T <sup>2</sup>
✓	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge5As38Te57 chalcogenide glass, Vacuum 59 (2000) 845-853.			
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	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag2Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.	
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
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	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810	
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				Art Unit	2529
				Examiner Name	Not Yet Assigned - Yevsi Kov
Sheet	3	of	8	Attorney Docket Number	M4065.0698/P698-A

✓		steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132.	
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Sheet	4	of	8	Attorney Docket Number	M4065.0698/P698-A

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			Filing Date	December 12, 2003	
			First Named Inventor	Kristy A. Campbell	
			Art Unit	2829	
			Examiner Name	Not Yet Assigned - Yelviskov	
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				Examiner Name	Not Yet Assigned Yevsi Kov
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		Art Unit	2825 2829 B		
		Examiner Name	R. Rocchegiani VYERS/Ka		
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		Examiner Name	R. Reochegiani Yevsikov		
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V9	**AU1	3,988,720	10/1976	Ovshinsky	
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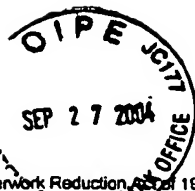
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		Application Number	10/736,617		
		Filing Date	December 17, 2003		
		First Named Inventor	Kristy A. Campbell		
		Art Unit	2823 9		
		Examiner Name	<del>R. Rocchegiani</del> Yeusikov		
Sheet	5	of	5	Attorney Docket Number	M4065.0698/P698-A

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>2</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
VY	**BA	JP 5-6126916	10/19981	Akira et al.		
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Examiner Signature	V. Yeusikov	Date Considered	03/01/05
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